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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	e200z0h
Core Size	32-Bit Single-Core
Speed	64MHz
Connectivity	CANbus, LINbus, SPI, UART/USART
Peripherals	DMA, POR, PWM, WDT
Number of I/O	64
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	20K x 8
Voltage - Supply (Vcc/Vdd)	4.5V ~ 5.5V
Data Converters	A/D 16x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/spc560p40l3ceaar

List of tables

Table 4. SPC560P34/SPC560P40 series block summary (continued)

Block	Function
Pulse width modulator (FlexPWM)	Contains four PWM submodules, each of which capable of controlling a single half-bridge power stage and two fault input channels
Reset generation module (MC_RGM)	Centralizes reset sources and manages the device reset sequence of the device
Static random-access memory (SRAM)	Provides storage for program code, constants, and variables
System integration unit lite (SIUL)	Provides control over all the electrical pad controls and up 32 ports with 16 bits of bidirectional, general-purpose input and output signals and supports up to 32 external interrupts with trigger event configuration
System status and configuration module (SSCM)	Provides system configuration and status data (such as memory size and status, device mode and security status), device identification data, debug status port enable and selection, and bus and peripheral abort enable/disable
System timer module (STM)	Provides a set of output compare events to support AUTOSAR(1) and operating system tasks
System watchdog timer (SWT)	Provides protection from runaway code
Wakeup unit (WKPU)	Supports up to 18 external sources that can generate interrupts or wakeup events, of which 1 can cause non-maskable interrupt requests or wakeup events

1. AUTOSAR: AUTomotive Open System ARchitecture (see www.autosar.org)

1.5 Feature details

1.5.1 High performance e200z0 core processor

The e200z0 Power Architecture core provides the following features:

- High performance e200z0 core processor for managing peripherals and interrupts
- Single issue 4-stage pipeline in-order execution 32-bit Power Architecture CPU
- Harvard architecture
- Variable length encoding (VLE), allowing mixed 16- and 32-bit instructions
  - Results in smaller code size footprint
  - Minimizes impact on performance
- Branch processing acceleration using lookahead instruction buffer
- Load/store unit
  - 1-cycle load latency
  - Misaligned access support
  - No load-to-use pipeline bubbles
- Thirty-two 32-bit general purpose registers (GPRs)
- Separate instruction bus and load/store bus Harvard architecture
- Hardware vectored interrupt support
- Reservation instructions for implementing read-modify-write constructs
- Long cycle time instructions, except for guarded loads, do not increase interrupt latency
- Extensive system development support through Nexus debug port
- Non-maskable interrupt support

1.5.2 Crossbar switch (XBAR)

The XBAR multi-port crossbar switch supports simultaneous connections between three master ports and three slave ports. The crossbar supports a 32-bit address bus width and a 32-bit data bus width.

The crossbar allows for two concurrent transactions to occur from any master port to any slave port; but one of those transfers must be an instruction fetch from internal flash memory. If a slave port is simultaneously requested by more than one master port, arbitration logic will select the higher priority master and grant it ownership of the slave port. All other masters requesting that slave port will be stalled until the higher priority master completes its transactions. Requesting masters will be treated with equal priority and will be granted access a slave port in round-robin fashion, based upon the ID of the last master to be granted access.

The flash memory module provides the following features:

- As much as 320 KB flash memory
  - 6 blocks (32 KB + 2×16 KB + 32 KB + 32 KB + 128 KB) code flash memory
  - 4 blocks (16 KB + 16 KB + 16 KB + 16 KB) data flash memory
  - Full Read-While-Write (RWW) capability between code flash memory and data flash memory
- Four 128-bit wide prefetch buffers to provide single cycle in-line accesses (prefetch buffers can be configured to prefetch code or data or both)
- Typical flash memory access time: no wait-state for buffer hits, 2 wait-states for page buffer miss at 64 MHz
- Hardware managed flash memory writes handled by 32-bit RISC Krypton engine
- Hardware and software configurable read and write access protections on a per-master basis
- Configurable access timing allowing use in a wide range of system frequencies
- Multiple-mapping support and mapping-based block access timing (up to 31 additional cycles) allowing use for emulation of other memory types
- Software programmable block program/erase restriction control
- Erase of selected block(s)
- Read page sizes
  - Code flash memory: 128 bits (4 words)
  - Data flash memory: 32 bits (1 word)
- ECC with single-bit correction, double-bit detection for data integrity
  - Code flash memory: 64-bit ECC
  - Data flash memory: 32-bit ECC
- Embedded hardware program and erase algorithm
- Erase suspend and program abort
- Censorship protection scheme to prevent flash memory content visibility
- Hardware support for EEPROM emulation

1.5.5 Static random access memory (SRAM)

The SPC560P34/SPC560P40 SRAM module provides up to 20 KB of general-purpose memory.

The SRAM module provides the following features:

- Supports read/write accesses mapped to the SRAM from any master
- Up to 20 KB general purpose SRAM
- Supports byte (8-bit), half word (16-bit), and word (32-bit) writes for optimal use of memory
- Typical SRAM access time: no wait-state for reads and 32-bit writes; 1 wait-state for 8- and 16-bit writes if back-to-back with a read to same memory block

2.2.3 Pin multiplexing

Table 7 defines the pin list and muxing for the SPC560P34/SPC560P40 devices.

Each row of *Table 7* shows all the possible ways of configuring each pin, via alternate functions. The default function assigned to each pin after reset is the ALT0 function.

SPC560P34/SPC560P40 devices provide three main I/O pad types, depending on the associated functions:

- *Slow pads* are the most common, providing a compromise between transition time and low electromagnetic emission.
- *Medium pads* provide fast enough transition for serial communication channels with controlled current to reduce electromagnetic emission.
- *Fast pads* provide maximum speed. They are used for improved NEXUS debugging capability.

Medium and Fast pads can use slow configuration to reduce electromagnetic emission, at the cost of reducing AC performance. For more information, see “Pad AC Specifications” in the device datasheet.

Table 7. Pin muxing

Port pin	PCR register	Alternate function[1],[2]	Functions	Peripheral[3]	I/O direction[4]	Pad speed[5]		Pin	
						SRC = 0	SRC = 1	64-pin	100-pin
Port A (16-bit)									
A[0]	PCR[0]	ALT0 ALT1 ALT2 ALT3 —	GPIO[0] ETC[0] SCK F[0] EIRQ[0]	SIUL eTimer_0 DSPI_2 FCU_0 SIUL	I/O I/O I/O O I	Slow	Medium	—	51
A[1]	PCR[1]	ALT0 ALT1 ALT2 ALT3 —	GPIO[1] ETC[1] SOUT F[1] EIRQ[1]	SIUL eTimer_0 DSPI_2 FCU_0 SIUL	I/O I/O O O I	Slow	Medium	—	52
A[2]	PCR[2]	ALT0 ALT1 ALT2 ALT3 — — —	GPIO[2] ETC[2] — A[3] SIN ABS[0] EIRQ[2]	SIUL eTimer_0 — FlexPWM_0 DSPI_2 MC_RGM SIUL	I/O I/O — O I I I	Slow	Medium	—	57
A[3]	PCR[3]	ALT0 ALT1 ALT2 ALT3 — —	GPIO[3] ETC[3] CS0 B[3] ABS[1] EIRQ[3]	SIUL eTimer_0 DSPI_2 FlexPWM_0 MC_RGM SIUL	I/O I/O I/O O I I	Slow	Medium	41	64

Table 7. Pin muxing (continued)

Port pin	PCR register	Alternate function[1],[2]	Functions	Peripheral[3]	I/O direction[4]	Pad speed[5]		Pin	
						SRC = 0	SRC = 1	64-pin	100-pin
E[4]	PCR[68]	ALT0 ALT1 ALT2 ALT3 —	GPIO[68] — — — AN[7]	SIUL — — — ADC_0	Input only	—	—	—	44
E[5]	PCR[69]	ALT0 ALT1 ALT2 ALT3 —	GPIO[69] — — — AN[8]	SIUL — — — ADC_0	Input only	—	—	—	43
E[6]	PCR[70]	ALT0 ALT1 ALT2 ALT3 —	GPIO[70] — — — AN[9]	SIUL — — — ADC_0	Input only	—	—	—	45
E[7]	PCR[71]	ALT0 ALT1 ALT2 ALT3 —	GPIO[71] — — — AN[10]	SIUL — — — ADC_0	Input only	—	—	—	41

1. ALT0 is the primary (default) function for each port after reset.
2. Alternate functions are chosen by setting the values of the PCR.PA bitfields inside the SIU module. PCR.PA = 00 → ALT0; PCR.PA = 01 → ALT1; PCR.PA = 10 → ALT2; PCR.PA = 11 → ALT3. This is intended to select the output functions; to use one of the input functions, the PCR.IBE bit must be written to '1', regardless of the values selected in the PCR.PA bitfields. For this reason, the value corresponding to an input only function is reported as "—".
3. Module included on the MCU.
4. Multiple inputs are routed to all respective modules internally. The input of some modules must be configured by setting the values of the PSMIO.PADSELx bitfields inside the SIUL module.
5. Programmable via the SRC (Slew Rate Control) bits in the respective Pad Configuration Register.
6. ADC0.AN emulates ADC1.AN. This feature is used to provide software compatibility between SPC560P34/SPC560P40 and SPC560P50. Refer to ADC chapter of reference manual for more details.

3 Electrical characteristics

3.1 Introduction

This section contains device electrical characteristics as well as temperature and power considerations.

This microcontroller contains input protection against damage due to high static voltages. However, it is advisable to take precautions to avoid application of any voltage higher than the specified maximum rated voltages.

To enhance reliability, unused inputs can be driven to an appropriate logic voltage level (V_{DD} or V_{SS}). This can be done by the internal pull-up or pull-down resistors, which are provided by the device for most general purpose pins.

The following tables provide the device characteristics and its demands on the system.

In the tables where the device logic provides signals with their respective timing characteristics, the symbol “CC” for Controller Characteristics is included in the Symbol column.

In the tables where the external system must provide signals with their respective timing characteristics to the device, the symbol “SR” for System Requirement is included in the Symbol column.

Caution:

All of the following parameter values can vary depending on the application and must be confirmed during silicon characterization or silicon reliability trial.

3.2 Parameter classification

The electrical parameters are guaranteed by various methods. To give the customer a better understanding, the classifications listed in *Table 8* are used and the parameters are tagged accordingly in the tables where appropriate.

Table 8. Parameter classifications

Classification tag	Tag description
P	Those parameters are guaranteed during production testing on each individual device.
C	Those parameters are achieved by the design characterization by measuring a statistically relevant sample size across process variations.
T	Those parameters are achieved by design characterization on a small sample size from typical devices under typical conditions unless otherwise noted. All values shown in the typical column are within this category.
D	Those parameters are derived mainly from simulations.

Note: The classification is shown in the column labeled “C” in the parameter tables where appropriate.

Table 15. Approved NPN ballast components

Part	Manufacturer	Approved derivatives(1)
BC817	Infineon	BC817-16; BC817-25; BC817SU
	NXP	BC817-16; BC817-25
BCP56	ST	BCP56-16
	Infineon	BCP56-10; BCP56-16
	ON Semi	BCP56-10
	NXP	BCP56-10; BCP56-16

1. For automotive applications please check with the appropriate transistor vendor for automotive grade certification

Table 16. Voltage regulator electrical characteristics

Symbol		C	Parameter	Conditions	Value			Unit
					Min	Typ	Max	
$V_{DD\_LV\_REGCOR}$	CC	P	Output voltage under maximum load run supply current configuration	Post-trimming	1.15	—	1.32	V
C_{DEC1}	SR	—	External decoupling/stability ceramic capacitor	BJT from *Table 15*. Three capacitors (i.e. X7R or X8R capacitors) with nominal value of 10 µF	19.5	30	—	µF
				BJT BC817, one capacitance of 22 µF	14.3	22	—	µF
R_{REG}	SR	—	Resulting ESR of either one or all three C_{DEC1}	Absolute maximum value between 100 kHz and 10 MHz	—	—	45	mΩ
C_{DEC2}	SR	—	External decoupling/stability ceramic capacitor	Four capacitances (i.e. X7R or X8R capacitors) with nominal value of 440 nF	1200	1760	—	nF
C_{DEC3}	SR	—	External decoupling/stability ceramic capacitor on VDD_HV_REG	Three capacitors (i.e. X7R or X8R capacitors) with nominal value of 10 µF; C_{DEC3} has to be equal or greater than C_{DEC1}	19.5	30	—	µF
L_{Reg}	SR	—	Resulting ESL of $V_{DD\_HV\_REG}$, BCTRL and $V_{DD\_LV\_CORx}$ pins	—	—	—	5	nH

memory and 16 MHz RC oscillator needed during power-up phase and reset phase. When POWER_OK is low the associated modules are set into a safe state.

Figure 11. Power-up typical sequence

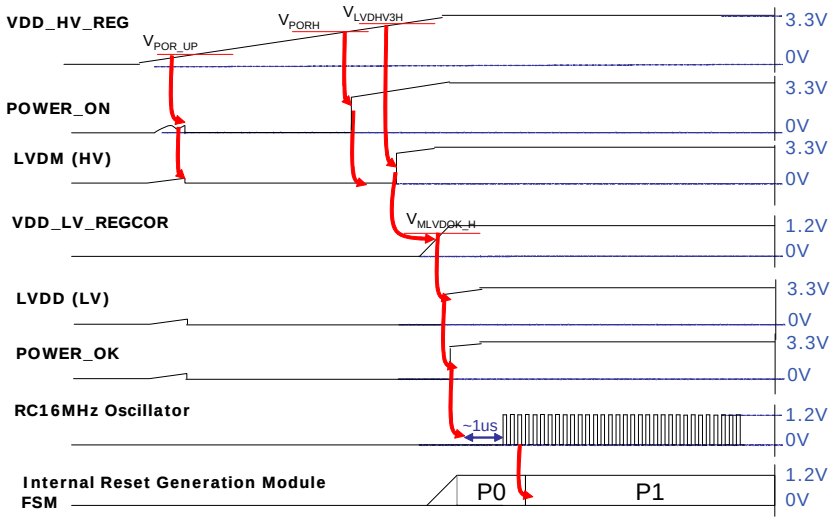
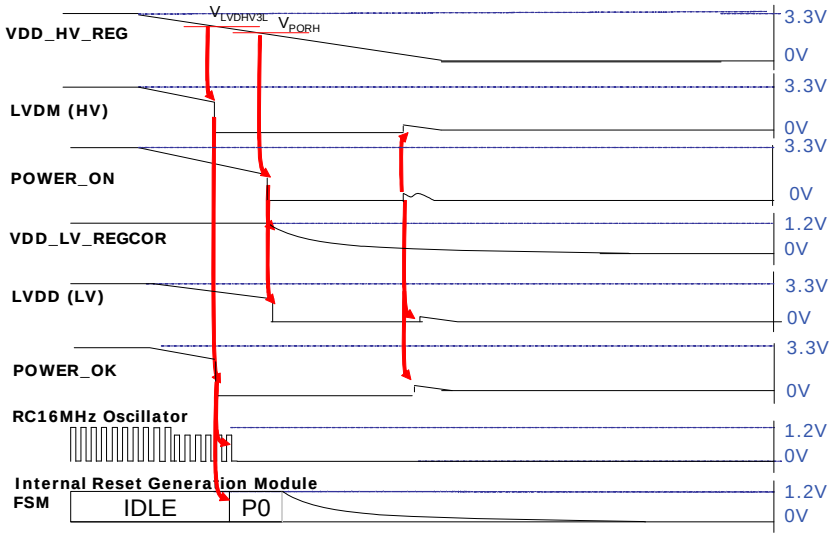


Figure 12. Power-down typical sequence



3.10.5 I/O pad current specification

The I/O pads are distributed across the I/O supply segment. Each I/O supply segment is associated to a V_{DD}/V_{SS} supply pair as described in *Table 23*.

Table 23. I/O supply segment

Package	Supply segment				
	1	2	3	4	5
LQFP100	pin15–pin26	pin27–pin46	pin51–pin61	pin64–pin86	pin89–pin10
LQFP64	pin8–pin17	pin18–pin30	pin33–pin38	pin41–pin54	pin57–pin5

Table 24. I/O consumption

Symbol		C	Parameter	Conditions[1]		Value			Unit
						Min	Typ	Max	
I_{SWTSLW}[2]	CC	D	Dynamic I/O current for SLOW configuration	C_L = 25 pF	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	20	mA
					V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	16	
I_{SWTMED}[2]	CC	D	Dynamic I/O current for MEDIUM configuration	C_L = 25 pF	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	29	mA
					V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	17	
I_{SWTFST}[2]	CC	D	Dynamic I/O current for FAST configuration	C_L = 25 pF	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	110	mA
					V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	50	
I_{RMSSLW}	CC	D	Root medium square I/O current for SLOW configuration	C_L = 25 pF, 2 MHz	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	2.3	mA
				C_L = 25 pF, 4 MHz		—	—	3.2	
				C_L = 100 pF, 2 MHz		—	—	6.6	
				C_L = 25 pF, 2 MHz	V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	1.6	
				C_L = 25 pF, 4 MHz		—	—	2.3	
				C_L = 100 pF, 2 MHz		—	—	4.7	
I_{RMSMED}	CC	D	Root medium square I/O current for MEDIUM configuration	C_L = 25 pF, 13 MHz	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	6.6	mA
				C_L = 25 pF, 40 MHz		—	—	13.4	
				C_L = 100 pF, 13 MHz		—	—	18.3	
				C_L = 25 pF, 13 MHz	V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	5	
				C_L = 25 pF, 40 MHz		—	—	8.5	
				C_L = 100 pF, 13 MHz		—	—	11	

In particular two different transient periods can be distinguished:

- A first and quick charge transfer from the internal capacitance C_{P1} and C_{P2} to the sampling capacitance C_S occurs (C_S is supposed initially completely discharged): considering a worst case (since the time constant in reality would be faster) in which C_{P2} is reported in parallel to C_{P1} (call $C_P = C_{P1} + C_{P2}$), the two capacitances C_P and C_S are in series, and the time constant is

Equation 5

$$\tau_1 = (R_{SW} + R_{AD}) \bullet \frac{C_P \bullet C_S}{C_P + C_S}$$

Equation 5 can again be simplified considering only C_S as an additional worst condition. In reality, the transient is faster, but the A/D converter circuitry has been designed to be robust also in the very worst case: the sampling time T_S is always much longer than the internal time constant:

Equation 6

$$\tau_1 < (R_{SW} + R_{AD}) \bullet C_S \ll T_S$$

The charge of C_{P1} and C_{P2} is redistributed also on C_S, determining a new value of the voltage V_{A1} on the capacitance according to *Equation 7*:

Equation 7

$$V_{A1} \bullet (C_S + C_{P1} + C_{P2}) = V_A \bullet (C_{P1} + C_{P2})$$

- A second charge transfer involves also C_F (that is typically bigger than the on-chip capacitance) through the resistance R_L: again considering the worst case in which C_{P2} and C_S were in parallel to C_{P1} (since the time constant in reality would be faster), the time constant is:

Equation 8

$$\tau_2 < R_L \bullet (C_S + C_{P1} + C_{P2})$$

In this case, the time constant depends on the external circuit: in particular imposing that the transient is completed well before the end of sampling time T_S, a constraints on R_L sizing is obtained:

Equation 9

$$8.5 \bullet \tau_2 = 8.5 \bullet R_L \bullet (C_S + C_{P1} + C_{P2}) < T_S$$

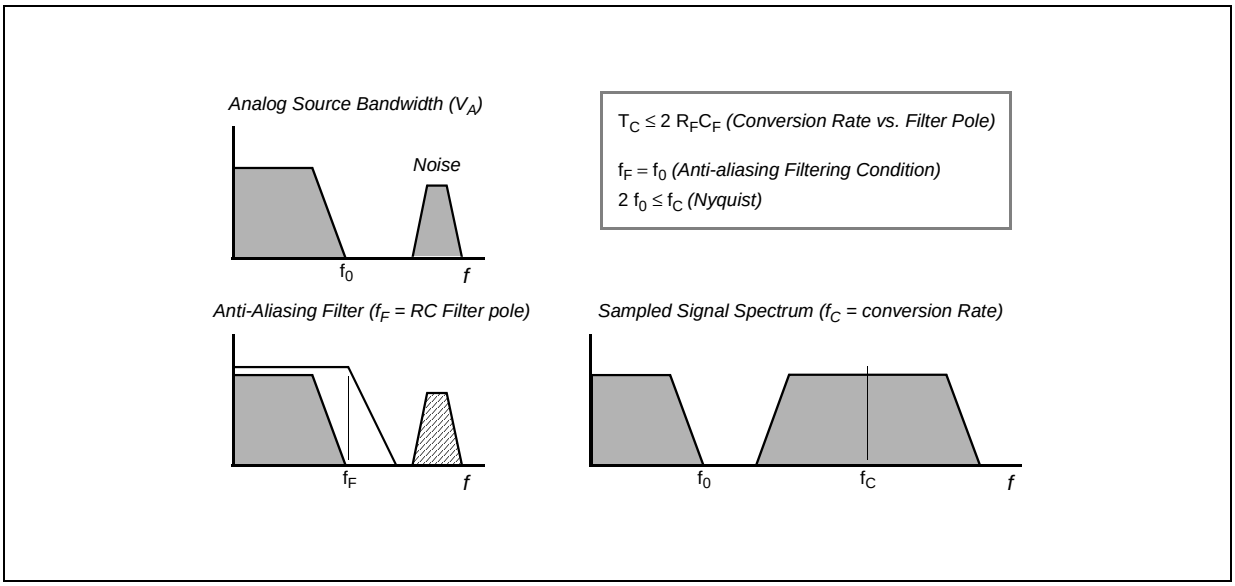
Of course, R_L shall be sized also according to the current limitation constraints, in combination with R_S (source impedance) and R_F (filter resistance). Being C_F definitively bigger than C_{P1}, C_{P2} and C_S, then the final voltage V_{A2} (at the end of the charge transfer transient) will be much higher than V_{A1}. *Equation 10* must be respected (charge balance assuming now C_S already charged at V_{A1}):

Equation 10

$$V_{A2} \bullet (C_S + C_{P1} + C_{P2} + C_F) = V_A \bullet C_F + V_{A1} \bullet (C_{P1} + C_{P2} + C_S)$$

The two transients above are not influenced by the voltage source that, due to the presence of the R_FC_F filter, is not able to provide the extra charge to compensate the voltage drop on C_S with respect to the ideal source V_A; the time constant R_FC_F of the filter is very high with respect to the sampling time (T_S). The filter is typically designed to act as anti-aliasing.

Figure 18. Spectral representation of input signal



Calling f_0 the bandwidth of the source signal (and as a consequence the cut-off frequency of the anti-aliasing filter, f_F), according to the Nyquist theorem the conversion rate f_C must be at least $2f_0$; it means that the constant time of the filter is greater than or at least equal to twice the conversion period (T_C). Again the conversion period T_C is longer than the sampling time T_S, which is just a portion of it, even when fixed channel continuous conversion mode is selected (fastest conversion rate at a specific channel): in conclusion it is evident that the time constant of the filter R_FC_F is definitively much higher than the sampling time T_S, so the charge level on C_S cannot be modified by the analog signal source during the time in which the sampling switch is closed.

The considerations above lead to impose new constraints on the external circuit, to reduce the accuracy error due to the voltage drop on C_S; from the two charge balance equations above, it is simple to derive *Equation 11* between the ideal and real sampled voltage on C_S:

Equation 11

$$\frac{V_A}{V_{A2}} = \frac{C_{P1} + C_{P2} + C_F}{C_{P1} + C_{P2} + C_F + C_S}$$

From this formula, in the worst case (when V_A is maximum, that is for instance 5 V), assuming to accept a maximum error of half a count, a constraint is evident on C_F value:

Equation 12

$$C_F > 2048 \bullet C_S$$

3.15.3 Start-up/Switch-off timings

Table 35. Start-up time/Switch-off time

Symbol		C	Parameter	Conditions[1]	Value			Unit
					Min	Typ	Max	
$T_{FLARSTEXIT}$	CC	T	Delay for Flash module to exit reset mode	Code flash memory	—	—	125	µs
		T		Data flash memory	—	—	125	
$T_{FLALPEXIT}$	CC	D	Delay for Flash module to exit low-power mode	Code flash memory	—	—	0.5	
$T_{FLAPDEXIT}$	CC	T	Delay for Flash module to exit power-down mode	Code flash memory	—	—	30	
		T		Data flash memory	—	—	30	
$T_{FLALPENTRY}$	CC	D	Delay for Flash module to enter low-power mode	Code flash memory	—	—	0.5	

1. V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified.

3.16 AC specifications

3.16.1 Pad AC specifications

Table 36. Output pin transition times

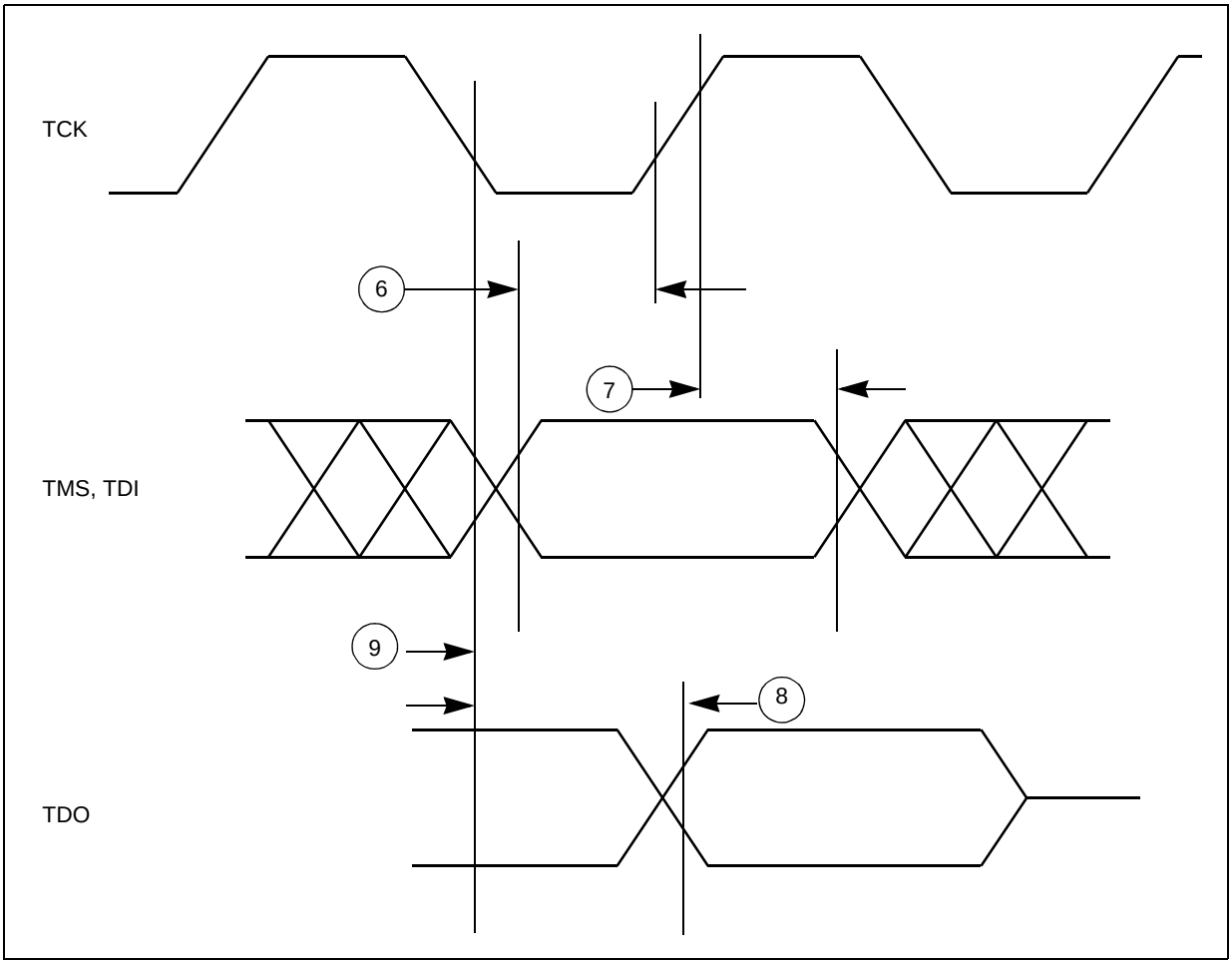
Symbol		C	Parameter	Conditions[1]		Value			Unit
						Min	Typ	Max	
t_{tr}	CC	D	Output transition time output pin[2] SLOW configuration	C_L = 25 pF	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	50	ns
		T		C_L = 50 pF		—	—	100	
		D		C_L = 100 pF		—	—	125	
		D		C_L = 25 pF	V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	40	
		T		C_L = 50 pF		—	—	50	
		D		C_L = 100 pF		—	—	75	
t_{tr}	CC	D	Output transition time output pin[2] MEDIUM configuration	C_L = 25 pF	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0 SIUL.PCRx.SRC = 1	—	—	10	ns
		T		C_L = 50 pF		—	—	20	
		D		C_L = 100 pF		—	—	40	
		D		C_L = 25 pF	V_{DD} = 3.3 V ± 10%, PAD3V5V = 1 SIUL.PCRx.SRC = 1	—	—	12	
		T		C_L = 50 pF		—	—	25	
		D		C_L = 100 pF		—	—	40	

Table 37. $\overline{\text{RESET}}$ electrical characteristics

Symbol		C	Parameter	Conditions[1]	Value[2]			Unit
					Min	Typ	Max	
V_{IH}	SR	P	Input high level CMOS (Schmitt Trigger)	—	$0.65V_{DD}$	—	V_{DD} + 0.4	V
V_{IL}	SR	P	Input low level CMOS (Schmitt Trigger)	—	–0.4	—	$0.35V_{DD}$	V
V_{HYS}	CC	C	Input hysteresis CMOS (Schmitt Trigger)	—	$0.1V_{DD}$	—	—	V
V_{OL}	CC	P	Output low level	Push Pull, I_{OL} = 2 mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 0 (recommended)	—	—	$0.1V_{DD}$	V
				Push Pull, I_{OL} = 1 mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 1[3]	—	—	$0.1V_{DD}$	
				Push Pull, I_{OL} = 1 mA, V_{DD} = 3.3 V ± 10%, PAD3V5V = 1 (recommended)	—	—	0.5	
t_{tr}	CC	D	Output transition time output pin[4] MEDIUM configuration	C_L = 25 pF, V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	10	ns
				C_L = 50 pF, V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	20	
				C_L = 100 pF, V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	40	
				C_L = 25 pF, V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	12	
				C_L = 50 pF, V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	25	
				C_L = 100 pF, V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	40	
W_{FRST}	SR	P	$\overline{\text{RESET}}$ input filtered pulse	—	—	—	40	ns
W_{NFRST}	SR	P	$\overline{\text{RESET}}$ input not filtered pulse	—	500	—	—	ns
t_{POR}	CC	D	Maximum delay before internal reset is released after all V_{DD_HV} reach nominal supply	Monotonic V_{DD_HV} supply ramp	—	—	1	ms
$\lvert I_{WPU} \rvert$	CC	P	Weak pull-up current absolute value	V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	10	—	150	µA
				V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	10	—	150	
				V_{DD} = 5.0 V ± 10%, PAD3V5V = 1[5]	10	—	250	

1. V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified
2. All values need to be confirmed during device validation.
3. This is a transient configuration during power-up, up to the end of reset PHASE2 (refer to RGM module section of device reference manual).

Figure 27. Nexus TDI, TMS, TDO timing



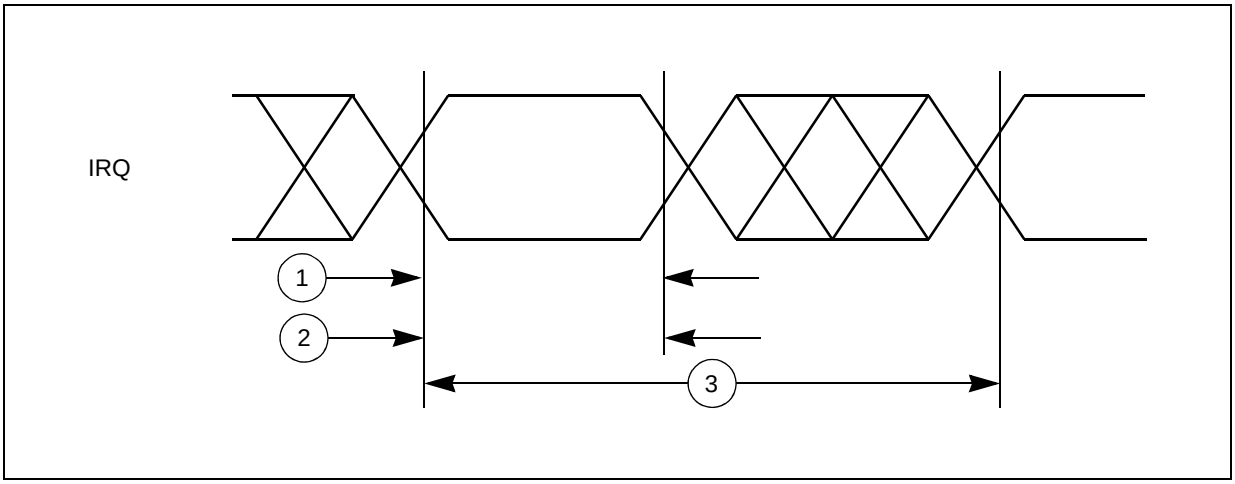
3.17.4 External interrupt timing (IRQ pin)

Table 40. External interrupt timing(1)

No.	Symbol		C	Parameter	Conditions	Value		Unit
						Min	Max	
1	t_{IPWL}	CC	D	IRQ pulse width low	—	4	—	t_{CYC}
2	t_{IPWH}	CC	D	IRQ pulse width high	—	4	—	t_{CYC}
3	t_{ICYC}	CC	D	IRQ edge to edge time(2)	—	4 + N (3)	—	t_{CYC}

1. IRQ timing specified at f_{SYS} = 64 MHz and $V_{DD\_HV\_IOx}$ = 3.0 V to 5.5 V, $T_A = T_L$ to T_H, and C_L = 200 pF with SRC = 0b00
2. Applies when IRQ pins are configured for rising edge or falling edge events, but not both.
3. N = ISR time to clear the flag

Figure 28. External interrupt timing



3.17.5 DSPI timing

Table 41. DSPI timing(1)

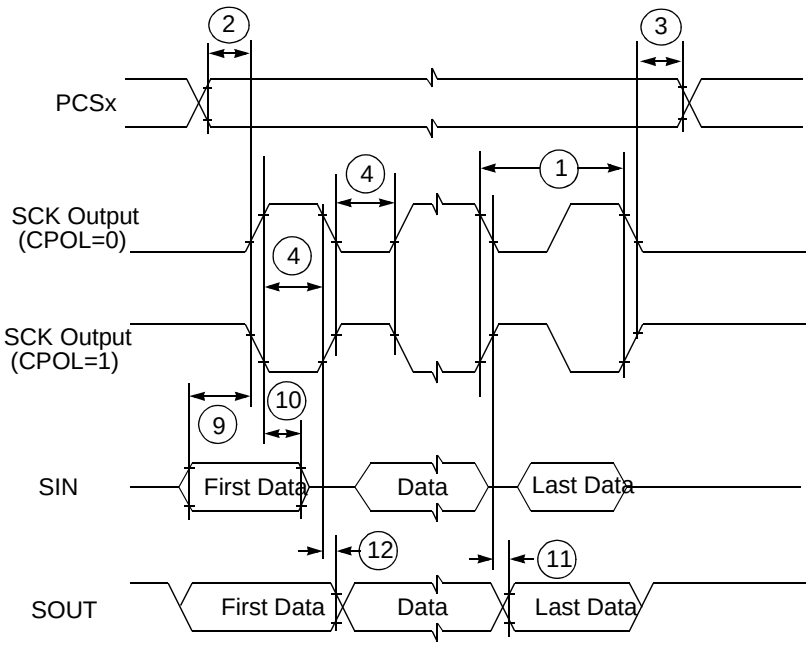
No.	Symbol		C	Parameter	Conditions	Value		Unit
						Min	Max	
1	t_{SCK}	CC	D	DSPI cycle time	Master (MTFE = 0)	60	—	ns
					Slave (MTFE = 0)	60	—	
2	t_{CSC}	CC	D	CS to SCK delay	—	16	—	ns
3	t_{ASC}	CC	D	After SCK delay	—	26	—	ns
4	t_{SDC}	CC	D	SCK duty cycle	—	0.4 * t_{SCK}	0.6 * t_{SCK}	ns
5	t_A	CC	D	Slave access time	$\overline{SS}$ active to SOUT valid	—	30	ns
6	t_{DIS}	CC	D	Slave SOUT disable time	$\overline{SS}$ inactive to SOUT high impedance or invalid	—	16	ns
7	t_{PCSC}	CC	D	PCSx to $\overline{PCSS}$ time	—	13	—	ns
8	t_{PASC}	CC	D	$\overline{PCSS}$ to PCSx time	—	13	—	ns
9	t_{SUI}	CC	D	Data setup time for inputs	Master (MTFE = 0)	35	—	ns
					Slave	4	—	
					Master (MTFE = 1, CPHA = 0)	35	—	
					Master (MTFE = 1, CPHA = 1)	35	—	
10	t_{HI}	CC	D	Data hold time for inputs	Master (MTFE = 0)	–5	—	ns
					Slave	4	—	
					Master (MTFE = 1, CPHA = 0)	11	—	
					Master (MTFE = 1, CPHA = 1)	–5	—	

Table 41. DSPI timing(1) (continued)

No.	Symbol		C	Parameter	Conditions	Value		Unit
						Min	Max	
11	t_{SUO}	CC	D	Data valid (after SCK edge)	Master (MTFE = 0)	—	12	ns
					Slave	—	36	
					Master (MTFE = 1, CPHA = 0)	—	12	
					Master (MTFE = 1, CPHA = 1)	—	12	
12	t_{HO}	CC	D	Data hold time for outputs	Master (MTFE = 0)	–2	—	ns
					Slave	6	—	
					Master (MTFE = 1, CPHA = 0)	6	—	
					Master (MTFE = 1, CPHA = 1)	–2	—	

1. All timing are provided with 50 pF capacitance on output, 1 ns transition time on input signal

Figure 29. DSPI classic SPI timing – Master, CPHA = 0



Note: Numbers shown reference *Table 41*.

Table 43. LQFP64 package mechanical data (continued)

Symbol	Dimensions					
	mm			inches[1]		
	Min	Typ	Max	Min	Typ	Max
k	0.0°	3.5°	7.0°	0.0°	3.5°	7.0°
ccc[2]	0.08			0.0031		

1. Values in inches are converted from millimeters (mm) and rounded to four decimal digits.
2. Tolerance

Appendix A Abbreviations

Table 44 lists abbreviations used in this document.

Table 44. Abbreviations

Abbreviation	Meaning
CMOS	Complementary metal–oxide–semiconductor
CPHA	Clock phase
CPOL	Clock polarity
CS	Peripheral chip select
DUT	Device under test
ECC	Error code correction
EVTO	Event out
GPIO	General purpose input / output
MC	Modulus counter
MCKO	Message clock out
MCU	Microcontroller unit
MDO	Message data out
MSEO	Message start/end out
MTFE	Modified timing format enable
NPN	Negative-positive-negative
NVUSRO	Non-volatile user options register
PTF	Post trimming frequency
PWM	Pulse width modulation
RISC	Reduced instruction set computer
SCK	Serial communications clock
SOUT	Serial data out
TBC	To be confirmed
TBD	To be defined
TCK	Test clock input
TDI	Test data input
TDO	Test data output
TMS	Test mode select

Revision history

Table 45. Document revision history

Date	Revision	Changes
01-Sep-2009	1	Initial release.
21-May-2010	2	Editorial updates Updated the following items in the “SPC560P34/SPC560P40 device comparison” table: – The heading – The “SRAM” row – The “FlexCAN” row – The “CTU” row – The “FlexPWM” row – The “LINFlex” row – The “DSPI” row – The “Nexus” row Updated the “SPC560P34/SPC560P40 device configuration difference” table: – Editorial updates – Added the “CTU” row – Deleted the “temperature” row – Swapped the content of Airbag and Full Featured cells Added the “Wakeup unit” block in the SPC560P34/SPC560P40 block diagram Updated the “Absolute Maximum Ratings“ table Updated the “Recommended operating conditions (5.0 V)“ table Updated the “Recommended operating conditions (3.3 V)“ table Updated the “Thermal characteristics for 100-pin LQFP“ table: – Ψ_{JT}: changed the typical value Updated the “EMI testing specifications“ table: replaced all values in “Level (Max)“ column with TBD Updated the “Electrical characteristics“ section: – Added the “Introduction” section – Added the “Parameter classification“ section – Added the “NVUSRO register“ section – Added the “Power supplies constraints (–0.3 V ≤ $V_{DD\_HV\_IOx}$ ≤ 6.0 V)” figure – Added the “Independent ADC supply (–0.3 V ≤ $V_{DD\_HV\_REG}$ ≤ 6.0 V)“ figure – Added the “Power supplies constraints (3.0 V ≤ $V_{DD\_HV\_IOx}$ ≤ 5.5 V)“ figure – Added the “Independent ADC supply (3.0 V ≤ $V_{DD\_HV\_REG}$ ≤ 5.5 V)“ figure Updated the “Power management electrical characteristics” section Updated the “Power Up/Down sequencing” section Updated the “DC electrical characteristics“ section – Deleted the “NVUSRO register” section – Updated the “DC electrical characteristics (5.0 V, NVUSRO[PAD3V5V] = 0)“ section: – Deleted all rows concerning $\overline{\text{RESET}}$ – Deleted “I_{VPP}“ row – Added the max value for C_{IN}